

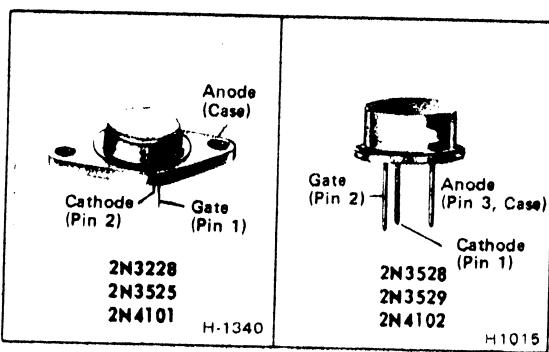
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## Thyristors

2N3228      2N3529  
2N3525      2N4101  
2N3528      2N4102



Current → Voltage ↓	Average Forward Amperes 3.2	Average Forward Amperes 1.3
For 120-Volt Line Operation	2N3228	2N3528
For 240-Volt Line Operation	2N3525	2N3529
For High- Voltage Power Supplies	2N4101	2N4102

**2N3228, 2N3525, 2N3528, 2N3529, 2N4101, 2N4102**

*Characteristics at Maximum Ratings (unless otherwise specified), and at Indicated Case Temperature ( $T_C$ )*

CHARACTERISTICS	CONTROLLED-RECTIFIER TYPES									UNITS	
	2N3228, 2N3528			2N3525, 2N3529			2N4101, 2N4102				
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.		
Forward Breakover Voltage, $V_{BOO}$ At $T_C = +100^\circ\text{C}$	200	—	—	400	—	—	600	—	—	volts	
Peak Blocking Current, at $T_C = +100^\circ\text{C}$	—	0.10	1.5	—	0.20	3.0	—	0.40	4.0	mA	
Forward, $I_{FBOM}$	—	0.05	0.75	—	0.10	1.5	—	0.20	2.0	mA	
$V_{FBOP} = V_{BOO}$ (min. value)	—	—	—	—	—	—	—	—	—	—	
Reverse, $I_{RBOM}$	—	—	—	—	—	—	—	—	—	—	
$V_{RBOP} = V_{RM}$ (rep) value	—	—	—	—	—	—	—	—	—	—	
Forward Voltage Drop, $v_F$ At a Forward Current of 30 amperes and a $T_C = +25^\circ\text{C}$	—	2.15	2.8	—	2.15	2.8	—	2.15	2.8	volts	
DC Gate-Trigger Current, $I_{GT}$ At $T_C = +25^\circ\text{C}$ (See Fig. 5)	—	8	15	—	8	15	—	8	15	mA(dc)	
Gate-Trigger Voltage, $V_{GT}$ At $T_C = +25^\circ\text{C}$ (See Fig. 5)	—	1.2	2.0	—	1.2	2.0	—	1.2	2.0	volts(dc)	
Holding Current, $I_{H00}$ At $T_C = +25^\circ\text{C}$	—	10	20	—	10	20	—	10	20	mA	
Critical Rate of Applied Forward Voltage, Critical $dv/dt$	10	200	—	10	200	—	10	200	—	volts/ microsecond	
$V_{FB} = V_{BOO}$ (min. value), exponential rise, $T_C = +100^\circ\text{C}$ (See waveshape of Fig. 2)	—	—	—	—	—	—	—	—	—	—	
Turn-On Time, $t_{on}$ , (Delay Time + Rise Time)	0.75	1.5	—	0.75	1.5	—	0.75	1.5	—	microseconds	
$V_{FB} = V_{BOO}$ (min. value), $I_F = 4.5$ amperes, $I_{GT} = 200$ mA, 0.1 .. s rise time, $T_C = +25^\circ\text{C}$ (See waveshapes of Fig. 3)	—	—	—	—	—	—	—	—	—	—	
Turn-Off Time, $t_{off}$ $I_F = 2$ amperes, 50 .. s pulse width, $dv_{FB}/dt = 20$ v/..s, $di/dt = 30$ A .. s, $I_{GT} = 200$ mA, $T_C = +75^\circ\text{C}$ (See waveshapes of Fig. 4)	—	15	50	—	15	50	—	15	50	microseconds	
2N3228, 2N3525, 2N4101									2N3528, 2N3529, 2N4102		
Thermal Resistance			Min.	Typ.	Max.	Min.	Typ.	Max.			
Junction-to-case	—	—	—	—	—	—	—	—	°C/W		
Junction-to-ambient	—	—	4	—	—	—	—	5	°C/W		
	—	—	40	—	—	—	—	40			

RATINGS	CONTROLLED-RECTIFIER TYPES						UNITS
	2N3228	2N3525	2N4101	2N3528	2N3529	2N4102	
Transient Peak Reverse Voltage (Non-Repetitive), $v_{RM}(\text{non-rep})$ . . . . .	330	660	700	330	660	700	volts
Peak Reverse Voltage (Repetitive), $v_{RM}(\text{rep})$ . . . . .	200	400	600	200	400	600	volts
Peak Forward Blocking Voltage (Repetitive), $v_{FBOM}(\text{rep})$ . . . . .	200	400	600	200	400	600	volts
Forward Current:							
For case temperature ( $T_C$ ) of + 75°C, and unit mounted on heat sink—							
Average DC value at a conduction angle of 180°, $I_{FAV}$ . . . . .	3.2	3.2	3.2	—	—	—	amperes
RMS value, $I_{FRMS}$ . . . . .	5.0	5.0	5.0	—	—	—	amperes
For other conditions, See Fig. 8							
For free-air temperature ( $T_{FA}$ ) of 25°C, and with no heat sink employed—							
Average DC value at a conduction angle of 180°, $I_{FAV}$ . . . . .	—	—	—	1.3	1.3	1.3	amperes
RMS value, $I_{FRMS}$ . . . . .	—	—	—	2.0	2.0	2.0	amperes
For other conditions, See Fig. 9							
Peak Surge Current, $I_{FM}(\text{surge})$ :							
For one cycle of applied principal voltage.							
60 Hz (sinusoidal), $T_C = 75^\circ\text{C}$ . . . . .	60			60			amperes
50 Hz (sinusoidal), $T_C = 75^\circ\text{C}$ . . . . .	50			50			amperes
For more than one cycle of applied voltage . . . . .				See Fig. 13		See Fig. 13	
Fusing Current (for SCR protection):							
$T_J = -40$ to $100^\circ\text{C}$ , $t = 1$ to $8.3 \text{ ns}$ , $I^2t$	15				15		ampere <sup>2</sup>
Rate of Change of Forward Current, $\frac{di}{dt}$ . . . . .				200		200	second
$V_{FB} = v_{BOO}$ (min. value)							amperes/
$I_{GT} = 200 \text{ mA}$ , $0.5 \mu\text{s}$ rise time (See waveshapes of Fig. 1)							microsecond
Gate Power*:							
Peak, Forward or Reverse, for $10 \mu\text{s}$ duration, $P_{GM}$ .				13		13	watts
(See Figs. 5 and 6)							
Average, $P_{GAV}$ . . . . .				0.5		0.5	watt
Temperature:							
Storage, $T_{STG}$ . . . . .				-40 to +125		-40 to +125	°C
Operating (Case), $T_C$ . . . . .				-40 to +100		-40 to +100	°C